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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
09/839,596	04/20/2001	Giuseppe Croce	99AG39853288	1496

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EXAMINER

NADAV, ORI

ART UNIT	PAPER NUMBER
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2811

DATE MAILED: 07/30/2003

Please find below and/or attached an Office communication concerning this application or proceeding.

# Office Action Summary

Applicati n No.

09/839,596

Applicant(s)

CROCE ET AL.

Examiner

ori nadav

Art Unit

2811

-- The MAILING DATE of this communication appears on the cover sheet with the correspondence address --

## Period for Reply

A SHORTENED STATUTORY PERIOD FOR REPLY IS SET TO EXPIRE 3 MONTH(S) FROM THE MAILING DATE OF THIS COMMUNICATION.

- Extensions of time may be available under the provisions of 37 CFR 1.136(a). In no event, however, may a reply be timely filed after SIX (6) MONTHS from the mailing date of this communication.
- If the period for reply specified above is less than thirty (30) days, a reply within the statutory minimum of thirty (30) days will be considered timely.
- If NO period for reply is specified above, the maximum statutory period will apply and will expire SIX (6) MONTHS from the mailing date of this communication.
- Failure to reply within the set or extended period for reply will, by statute, cause the application to become ABANDONED (35 U.S.C. § 133).
- Any reply received by the Office later than three months after the mailing date of this communication, even if timely filed, may reduce any earned patent term adjustment. See 37 CFR 1.704(b).

## Status

- 1) ☒ Responsive to communication(s) filed on 05 June 2003.
- 2a) ☐ This action is **FINAL**. 2b) ☒ This action is non-final.
- 3) ☐ Since this application is in condition for allowance except for formal matters, prosecution as to the merits is closed in accordance with the practice under *Ex parte Quayle*, 1935 C.D. 11, 453 O.G. 213.

## Disposition of Claims

- 4) ☒ Claim(s) 5-25 is/are pending in the application.
- 4a) Of the above claim(s) 19-25 is/are withdrawn from consideration.
- 5) ☐ Claim(s) \_\_\_\_\_ is/are allowed.
- 6) ☒ Claim(s) 5-18 is/are rejected.
- 7) ☐ Claim(s) \_\_\_\_\_ is/are objected to.
- 8) ☐ Claim(s) \_\_\_\_\_ are subject to restriction and/or election requirement.

## Application Papers

- 9) ☐ The specification is objected to by the Examiner.
- 10) ☐ The drawing(s) filed on \_\_\_\_\_ is/are: a) ☐ accepted or b) ☐ objected to by the Examiner.
- Applicant may not request that any objection to the drawing(s) be held in abeyance. See 37 CFR 1.85(a).
- 11) ☐ The proposed drawing correction filed on \_\_\_\_\_ is: a) ☐ approved b) ☐ disapproved by the Examiner.
- If approved, corrected drawings are required in reply to this Office action.
- 12) ☐ The oath or declaration is objected to by the Examiner.

## Priority under 35 U.S.C. §§ 119 and 120

- 13) ☐ Acknowledgment is made of a claim for foreign priority under 35 U.S.C. § 119(a)-(d) or (f).
- a) ☐ All b) ☐ Some \* c) ☐ None of:
1. ☐ Certified copies of the priority documents have been received.
2. ☐ Certified copies of the priority documents have been received in Application No. \_\_\_\_\_.
3. ☐ Copies of the certified copies of the priority documents have been received in this National Stage application from the International Bureau (PCT Rule 17.2(a)).
- \* See the attached detailed Office action for a list of the certified copies not received.
- 14) ☐ Acknowledgment is made of a claim for domestic priority under 35 U.S.C. § 119(e) (to a provisional application).
- a) ☐ The translation of the foreign language provisional application has been received.
- 15) ☐ Acknowledgment is made of a claim for domestic priority under 35 U.S.C. §§ 120 and/or 121.

## Attachment(s)

- 1) ☒ Notice of References Cited (PTO-892)
- 2) ☐ Notice of Draftsperson's Patent Drawing Review (PTO-948)
- 3) ☐ Information Disclosure Statement(s) (PTO-1449) Paper No(s) \_\_\_\_\_
- 4) ☐ Interview Summary (PTO-413) Paper No(s). \_\_\_\_\_
- 5) ☐ Notice of Informal Patent Application (PTO-152)
- 6) ☐ Other: \_\_\_\_\_

## DETAILED ACTION

### ***Claim Rejections - 35 USC § 102***

1. The following is a quotation of the appropriate paragraphs of 35 U.S.C. 102 that form the basis for the rejections under this section made in this Office action:

A person shall be entitled to a patent unless --

(b) the invention was patented or described in a printed publication in this or a foreign country or in public use or on sale in this country, more than one year prior to the date of application for patent in the United States.

2. Claim 5 is rejected under 35 U.S.C. 102(b) as anticipated by Huang (5,665,988).

Regarding claim 5, Huang teaches in figure 1 and related text lateral diffused metal oxide semiconductor (LDMOS) integrated device comprising: a semiconductor substrate 1; a drain region 2 of a first conductivity type n- adjacent the semiconductor substrate and comprising a superficial buffer region 13 being more heavily doped n than adjacent portions of the drain region; a body region 9 completely surrounded on a bottom and sides thereof by the buffer region 13 and having a second conductivity type p; and a source region 11 in the body region 9 and having the first conductivity type n+.

***Claim Rejections - 35 USC ' 103***

3. The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:

(a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which the subject matter pertains. Patentability shall not be negated by the manner in which the invention was made.

4. Claims 6-11 and 14-18 are rejected under 35 U.S.C. 103(a) as being unpatentable over Huang

Regarding claims 7, 9 and 14, Huang teaches substantially the entire claimed structure, as applied to claim 5 above, except a superficial buffer region having a dopant concentration of about  $5E16$  to  $5E17$  atoms  $cm^{-3}$  and the adjacent portions of the drain region having a dopant concentration of about  $2.5E15$  to  $2.5E16$  atoms  $cm^{-3}$ . It would have been obvious to a person of ordinary skill in the art at the time the invention was made to form a superficial buffer region having a dopant concentration of about  $5E16$  to  $5E17$  atoms  $cm^{-3}$  and the adjacent portions of the drain region having a dopant concentration of about  $2.5E15$  to  $2.5E16$  atoms  $cm^{-3}$ , in Huang's device, because it well within the skills of an artisan to adjust the relative concentrations of the superficial buffer region and the drain region in order to optimize the device characteristics. Note that differences in concentration do not support the patentability of subject matter encompassed by the prior art unless there is evidence indicating such concentration or temperature is critical. "[W]here the general conditions of a claim are

disclosed in the prior art, it is not inventive to discover the optimum or workable ranges by routine experimentation." In re Aller , 220 F.2d 454, 105 USPQ 233, 235 (CCPA 1955). See also In re Hoeschele , 406 F.2d 1403, 160 USPQ 809 (CCPA 1969). For more recent cases applying this principle, see Merck & Co. Inc . v. Biocraft Laboratories Inc. , 874 F.2d 804, 10 USPQ2d 1843 (Fed. Cir.), cert. denied , 493 U.S. 975 (1989), and In re Kulling , 897 F.2d 1147, 14 USPQ2d 1056 (Fed. Cir. 1990).

Regarding claims 6 and 15, Huang teaches substantially the entire claimed structure, as respectively applied to claims 5 and 14 above, except a drain region having a depth of about 1.5 to 4.5 micrometers. It would have been obvious to a person of ordinary skill in the art at the time the invention was made to use a drain region having a depth of about 1.5 to 4.5 micrometers, in Huang's device, in order to use the device in an application which requires a specific reverse voltage characteristics.

Regarding claims 8 and 16, Huang teaches substantially the entire claimed structure, as respectively applied to claims 5 and 14 above, except a superficial buffer region having a depth of about 0.15 to 0.45 micrometers. It would have been obvious to a person of ordinary skill in the art at the time the invention was made to use a superficial buffer region having a depth of about 1.5 to 4.5 micrometers, in Huang's device, in order to adjust the ON resistance such that optimum characteristics of the device can be obtained, and in order to use the device in an application which requires certain switching speed.

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Regarding claims 10 and 17, Huang teaches substantially the entire claimed structure, as respectively applied to claims 5 and 14 above, except a body region having a depth of about 0.25 to 0.75 micrometers. It would have been obvious to a person of ordinary skill in the art at the time the invention was made to use a body region having a depth of about 1.5 to 4.5 micrometers, in Huang's device, because it well within the skills of an artisan to adjust the relative thicknesses of the device's regions in order to optimize the device characteristics.

Regarding claims 11 and 18, Huang teaches substantially the entire claimed structure, as respectively applied to claims 5 and 14 above, except a body region having a dopant concentration of about  $5E17$  to  $5E18$  atoms  $cm^{-3}$ . It would have been obvious to a person of ordinary skill in the art at the time the invention was made to form a body region having a dopant concentration of about  $5E17$  to  $5E18$  atoms  $cm^{-3}$ , in Huang's device, because it well within the skills of an artisan to adjust the relative concentration of the body region in order to optimize the device characteristics. Note that differences in concentration do not support the patentability of subject matter encompassed by the prior art unless there is evidence indicating such concentration or temperature is critical. "[W]here the general conditions of a claim are disclosed in the prior art, it is not inventive to discover the optimum or workable ranges by routine experimentation." In re Aller, 220 F.2d 454, 105 USPQ 233, 235 (CCPA 1955). See also In re Hoeschele, 406 F.2d 1403, 160 USPQ 809 (CCPA 1969). For more recent cases applying this principle, see Merck & Co. Inc. v. Biocraft Laboratories Inc., 874 F.2d 804, 10

USPQ2d 1843 (Fed. Cir.), cert. denied, 493 U.S. 975 (1989), and In re Kulling, 897 F.2d 1147, 14 USPQ2d 1056 (Fed. Cir. 1990).

5. Claims 12 and 13 are rejected under 35 U.S.C. 103(a) as being unpatentable over Huang in view of Contiero et al. (5,041,895).

Regarding claim 12, Huang does not teach a drain region doped with phosphorous and wherein the body region is doped with boron. Contiero et al. teach in figure 1 a drain region doped with phosphorous and a body region doped with boron. It would have been obvious to a person of ordinary skill in the art at the time the invention was made to dope the drain region with phosphorous and the body region with boron, in Huang's device, because phosphorous and boron are conventional doping materials, of which official notice is taken.

Regarding claim 13, Huang teaches substantially the entire claimed structure, as applied to claim 5 above, except a drain region doped with boron and a body region doped with phosphorus. That is, Huang does not reverse the polarity of the transistor. Contiero et al. teach in figure 1 a complementary LDMOS (i.e. n-channel and p-channel LDMOS transistors). It would have been obvious to a person of ordinary skill in the art at the time the invention was made to dope the drain region with boron and the body region with phosphorus, in Huang's device, in order to use the device in an application which requires a complementary LDMOS device.

***R sponds to Arguments***

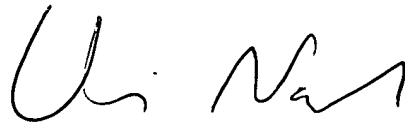
6. Applicant's arguments with respect to claims 5-18 have been considered but are moot in view of the new ground(s) of rejection.

**Papers related to this application may be submitted to Technology center (TC) 2800 by facsimile transmission. Papers should be faxed to TC 2800 via the TC 2800 Fax center located in Crystal Plaza 4, room 4-C23. The faxing of such papers must conform with the notice published in the Official Gazette, 1096 OG 30 (November 15, 1989). The Group 2811 Fax Center number is (703) 308-7722 and 308-7724. The Group 2811 Fax Center is to be used only for papers related to Group 2811 applications.**

Any inquiry concerning this communication or any earlier communication from the Examiner should be directed to *Examiner Nadav* whose telephone number is **(703) 308-8138**. The Examiner is in the Office generally between the hours of 7 AM to 4 PM (Eastern Standard Time) Monday through Friday. If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Tom Thomas, can be reached at **(703) 308-2772**.

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Any inquiry of a general nature or relating to the status of this application should be directed to the **Technology Center Receptionists** whose telephone number is **308-0956**.

A handwritten signature in black ink, appearing to read "Ori Nadav". The signature is fluid and cursive, with the first name "Ori" and last name "Nadav" clearly distinguishable.

O.N.  
July 15, 2003

ORI NADAV  
PATENT EXAMINER  
TECHNOLOGY CENTER 2800